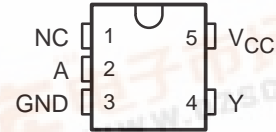


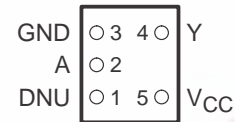
- Available in the Texas Instruments NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 3.5 ns at 3.3 V
- Low Power Consumption, 10- μ A Max I_{CC}
- ± 24 -mA Output Drive at 3.3 V
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DBV OR DCK PACKAGE
(TOP VIEW)



NC – No internal connection

YEP OR YZP PACKAGE
(BOTTOM VIEW)



DNU – Do not use

description/ordering information

This single buffer gate is designed for 1.65-V to 5.5-V V_{CC} operation. The SN74LVC1G34 performs the Boolean function $Y = A$ in positive logic.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING‡
–40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Reel of 3000	SN74LVC1G34YEPR	---C9_
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC1G34YZPR	
	SOT (SOT-23) – DBV	Reel of 3000	SN74LVC1G34DBVR	C34_
		Reel of 250	SN74LVC1G34DBVT	
	SOT (SC-70) – DCK	Reel of 3000	SN74LVC1G34DCKR	C9_
		Reel of 250	SN74LVC1G34DCKT	

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

‡ DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site.

YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoStar and NanoFree are trademarks of Texas Instruments.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

SN74LVC1G34

SINGLE BUFFER GATE

SCES519A – DECEMBER 2003 – REVISED JUNE 2004

FUNCTION TABLE

INPUT A	OUTPUT Y
H	H
L	L

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	-0.5 V to 6.5 V
Input voltage range, V_I (see Note 1)	-0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1)	-0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2)	-0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$)	-50 mA
Output clamp current, I_{OK} ($V_O < 0$)	-50 mA
Continuous output current, I_O	± 50 mA
Continuous current through V_{CC} or GND	± 100 mA
Package thermal impedance, θ_{JA} (see Note 3): DBV package	206°C/W
DCK package	252°C/W
YEP/YZP package	132°C/W
Storage temperature range, T_{stg}	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
 2. The value of V_{CC} is provided in the recommended operating conditions table.
 3. The package thermal impedance is calculated in accordance with JESD 51-7.

SN74LVC1G34 SINGLE BUFFER GATE

SCES519A – DECEMBER 2003 – REVISED JUNE 2004

recommended operating conditions (see Note 4)

		MIN	MAX	UNIT	
V _{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 3 V to 3.6 V	2		
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	0.7		
		V _{CC} = 3 V to 3.6 V	0.8		
		V _{CC} = 4.5 V to 5.5 V	0.3 × V _{CC}		
V _I	Input voltage	0	5.5	V	
V _O	Output voltage	0	V _{CC}	V	
I _{OH}	High-level output current	V _{CC} = 1.65 V	-4		mA
		V _{CC} = 2.3 V	-8		
		V _{CC} = 3 V	-16		
			-24		
		V _{CC} = 4.5 V	-32		
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4		mA
		V _{CC} = 2.3 V	8		
		V _{CC} = 3 V	16		
			24		
		V _{CC} = 4.5 V	32		
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V	20		ns/V
		V _{CC} = 3.3 V ± 0.3 V	10		
		V _{CC} = 5 V ± 0.5 V	10		
T _A	Operating free-air temperature	-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

SN74LVC1G34

SINGLE BUFFER GATE

SCES519A – DECEMBER 2003 – REVISED JUNE 2004

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
V _{OH}	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1			V
	I _{OH} = -4 mA	1.65 V	1.2			
	I _{OH} = -8 mA	2.3 V	1.9			
	I _{OH} = -16 mA	3 V	2.4			
	I _{OH} = -24 mA		2.3			
	I _{OH} = -32 mA	4.5 V	3.8			
V _{OL}	I _{OL} = 100 μA	1.65 V to 5.5 V			0.1	V
	I _{OL} = 4 mA	1.65 V			0.45	
	I _{OL} = 8 mA	2.3 V			0.3	
	I _{OL} = 16 mA	3 V			0.4	
	I _{OL} = 24 mA				0.55	
	I _{OL} = 32 mA	4.5 V			0.55	
I _I	V _I = 5.5 V or GND	0 to 5.5 V			±1	μA
I _{off}	V _I or V _O = 5.5 V	0			±10	μA
I _{CC}	V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V			10	μA
ΔI _{CC}	One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μA
C _i	V _I = V _{CC} or GND	3.3 V			3.5	pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	2	9.9	1.5	6	1	3.5	1	2.9	ns

switching characteristics over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	3.2	8.6	1.5	4.4	1.5	4.1	1	3.2	ns

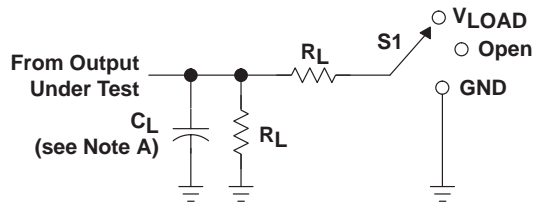
operating characteristics, T_A = 25°C

PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
		TYP	TYP	TYP	TYP	
C _{pd} Power dissipation capacitance	f = 10 MHz	16	16	16	18	pF

SN74LVC1G34 SINGLE BUFFER GATE

SCES519A – DECEMBER 2003 – REVISED JUNE 2004

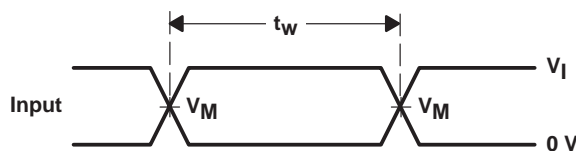
PARAMETER MEASUREMENT INFORMATION



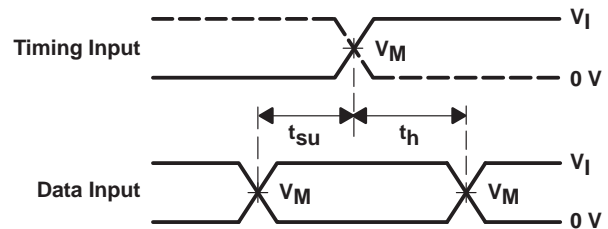
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

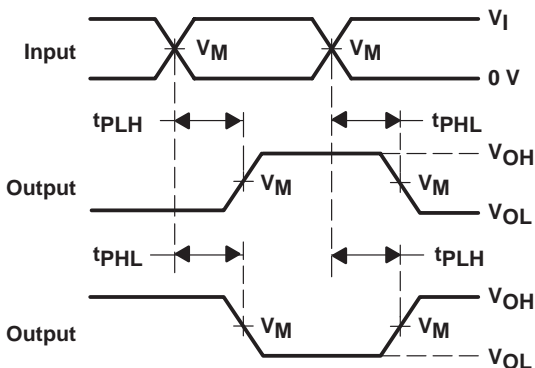
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8 V \pm 0.15 V$	V_{CC}	$\leq 2 \text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$2.5 V \pm 0.2 V$	V_{CC}	$\leq 2 \text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$3.3 V \pm 0.3 V$	3 V	$\leq 2.5 \text{ ns}$	1.5 V	6 V	15 pF	1 M Ω	0.3 V
$5 V \pm 0.5 V$	V_{CC}	$\leq 2.5 \text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.3 V



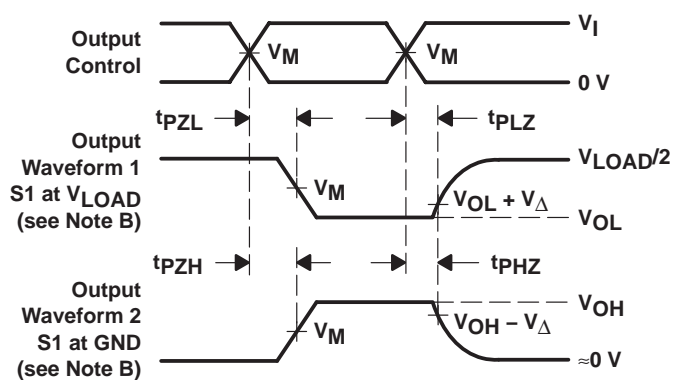
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

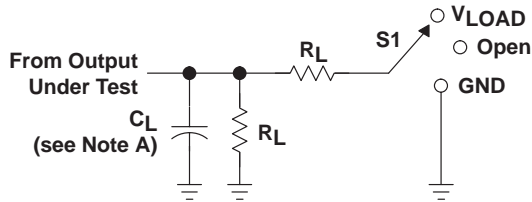
- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

SN74LVC1G34 SINGLE BUFFER GATE

SCES519A – DECEMBER 2003 – REVISED JUNE 2004

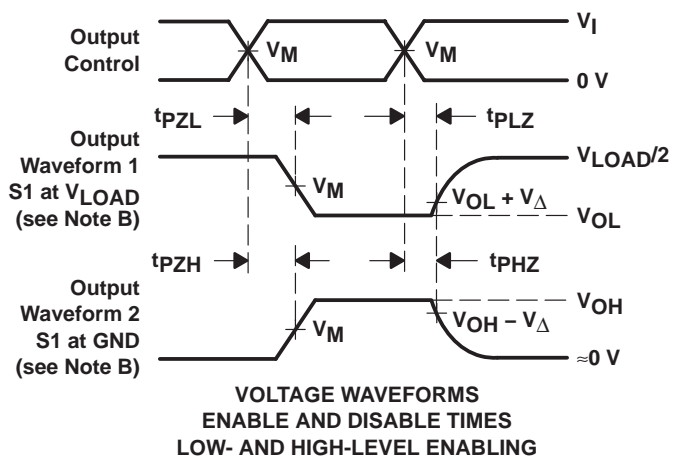
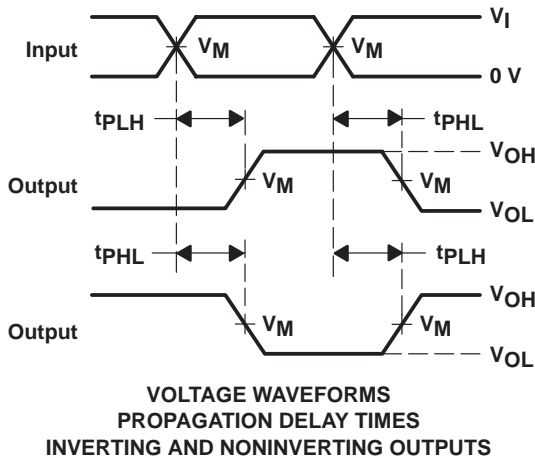
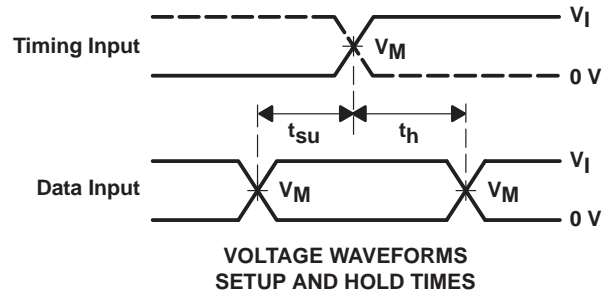
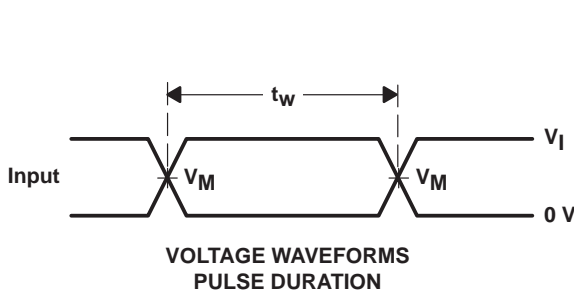
PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8 V \pm 0.15 V$	V_{CC}	$\leq 2 \text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5 V \pm 0.2 V$	V_{CC}	$\leq 2 \text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3 V \pm 0.3 V$	3 V	$\leq 2.5 \text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5 V \pm 0.5 V$	V_{CC}	$\leq 2.5 \text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN74LVC1G34DBVR	ACTIVE	SOT-23	DBV	5	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC1G34DBVT	ACTIVE	SOT-23	DBV	5	250	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC1G34DCKR	ACTIVE	SC70	DCK	5	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC1G34DCKT	ACTIVE	SC70	DCK	5	250	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC1G34YEPR	ACTIVE	WCSP	YEP	5	3000	None	SNPB	Level-1-260C-UNLIM
SN74LVC1G34YZPR	ACTIVE	WCSP	YZP	5	3000	Pb-Free (RoHS)	SNAGCU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - May not be currently available - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

None: Not yet available Lead (Pb-Free).

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean "Pb-Free" and in addition, uses package materials that do not contain halogens, including bromine (Br) or antimony (Sb) above 0.1% of total product weight.

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

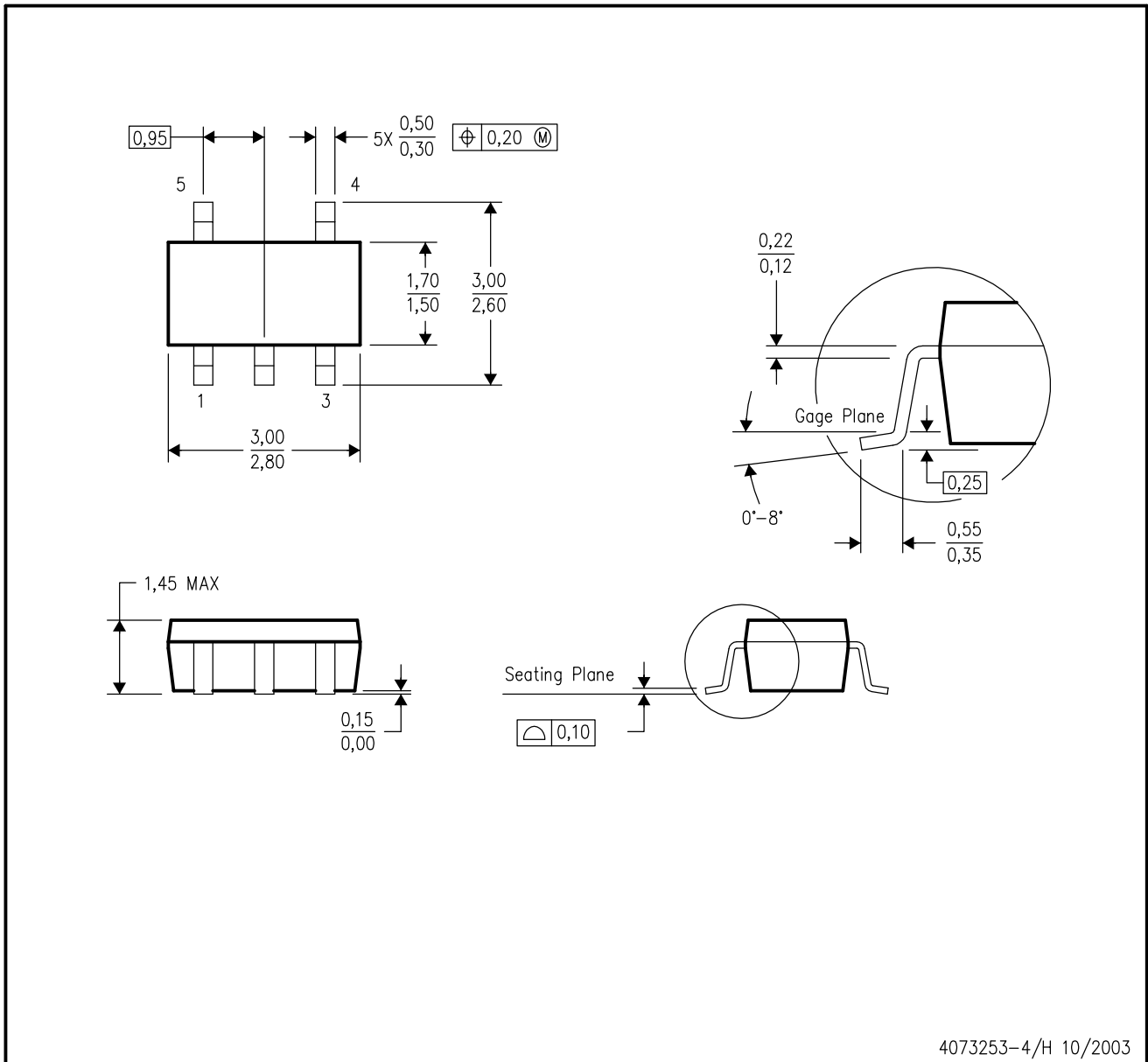
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MECHANICAL DATA

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



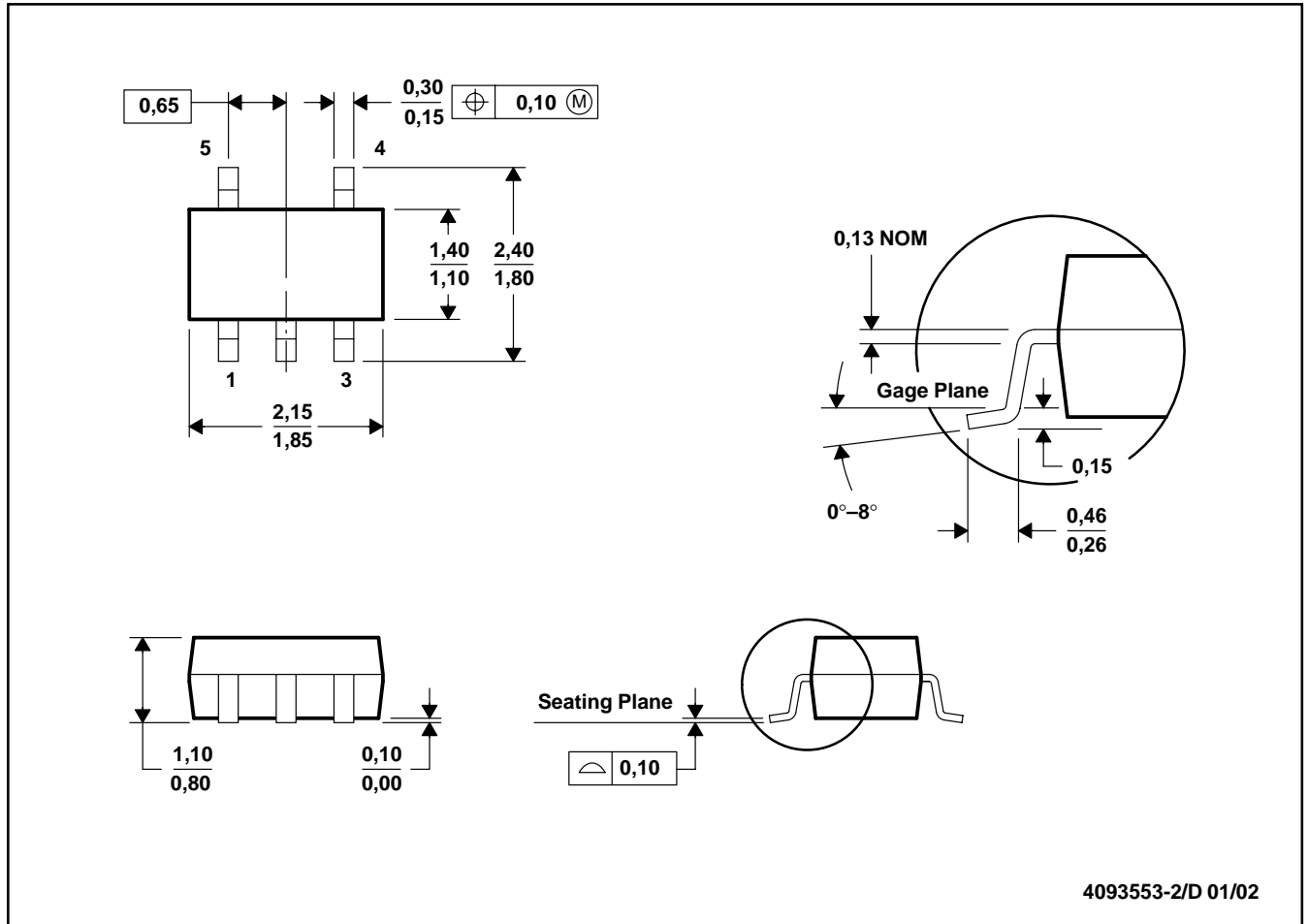
- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion.
 - D. Falls within JEDEC MO-178 Variation AA.

MECHANICAL DATA

MPDS025C – FEBRUARY 1997 – REVISED FEBRUARY 2002

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE

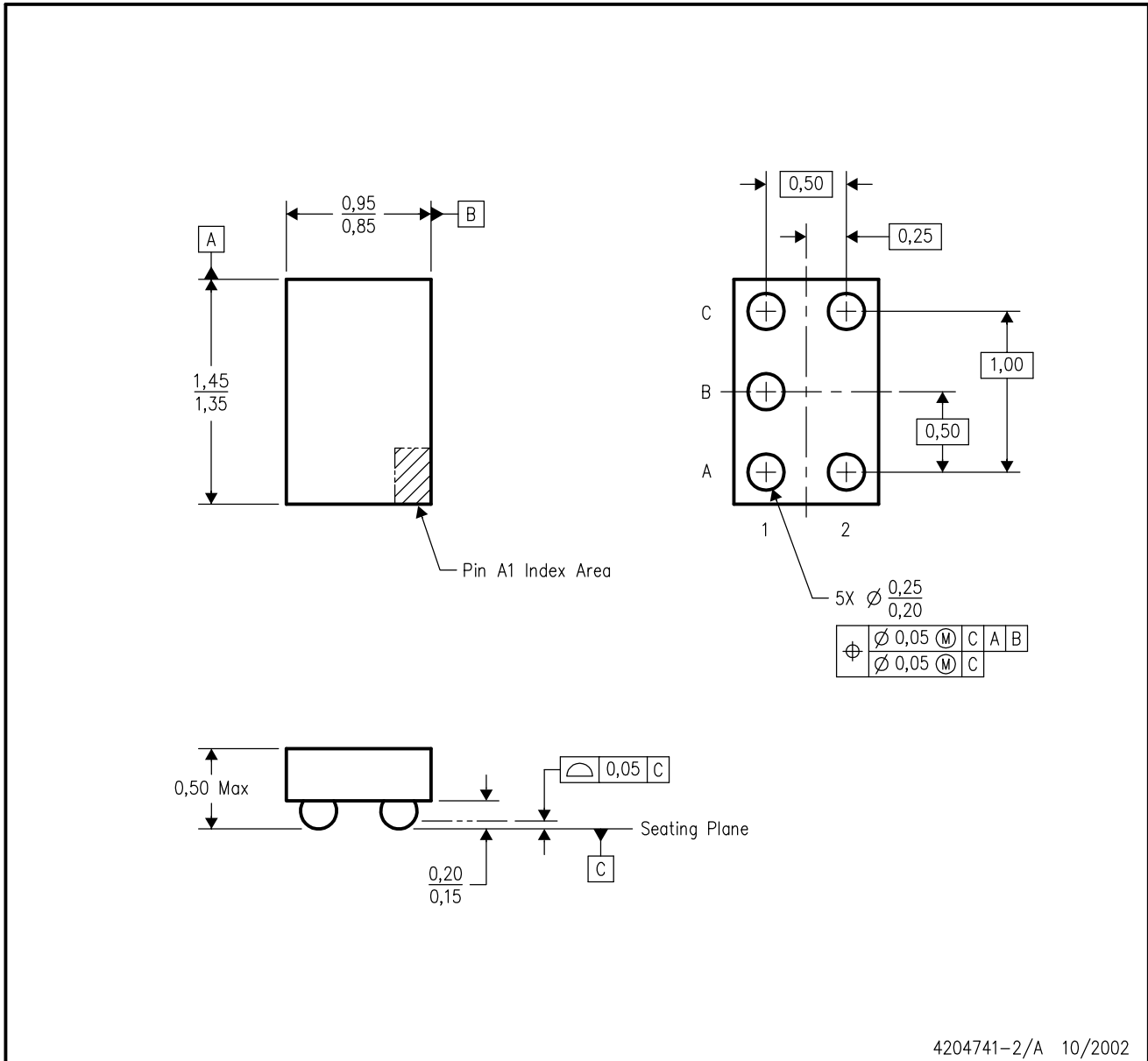


- NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion.
D. Falls within JEDEC MO-203

MECHANICAL DATA

YZP (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY

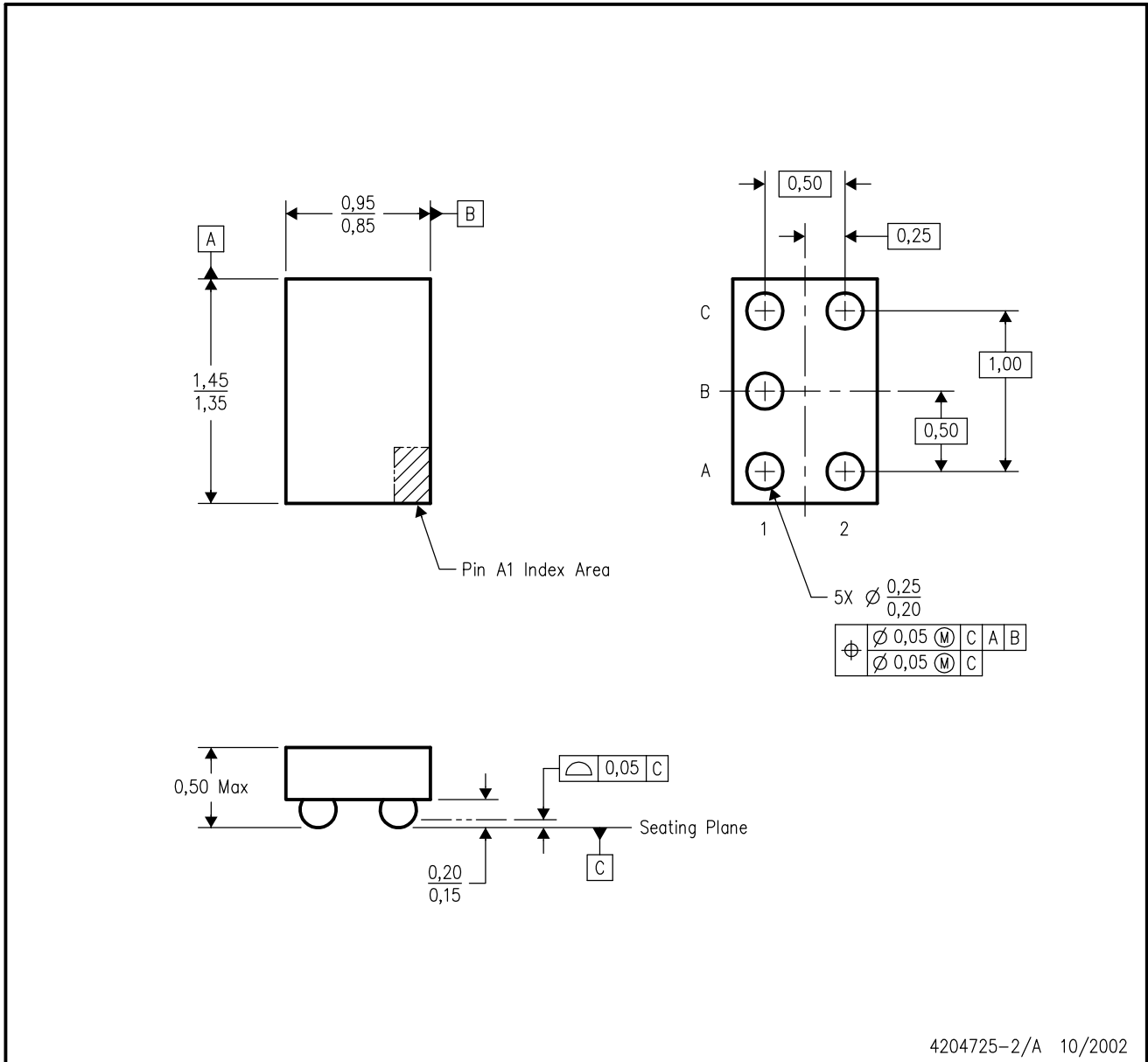


- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. This package is lead-free. Refer to the 5 YEP package (drawing 4204725) for tin-lead (SnPb).

MECHANICAL DATA

YEP (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoStar™ package configuration.
 - D. This package is tin-lead (SnPb). Refer to the 5 YZP package (drawing 4204741) for lead-free.

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